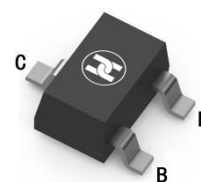
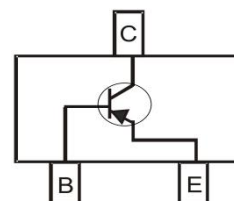


BIPOLAR TRANSISTOR (PNP)
FEATURES

- Complementary to MMST3904
- Excellent h_{FE} Linearity
- Low Noise
- Surface Mount device


SOT-323

MECHANICAL DATA

- Case: SOT-323
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

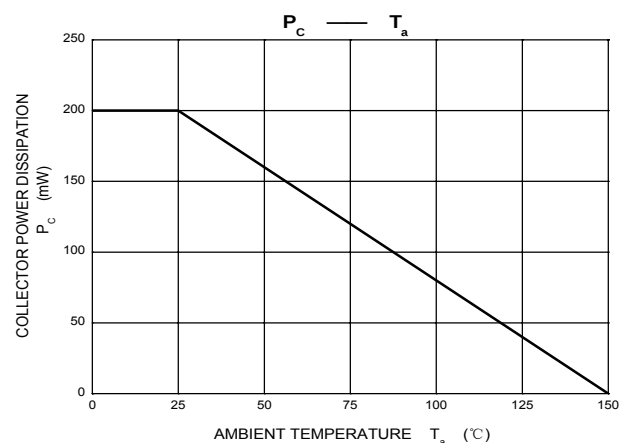
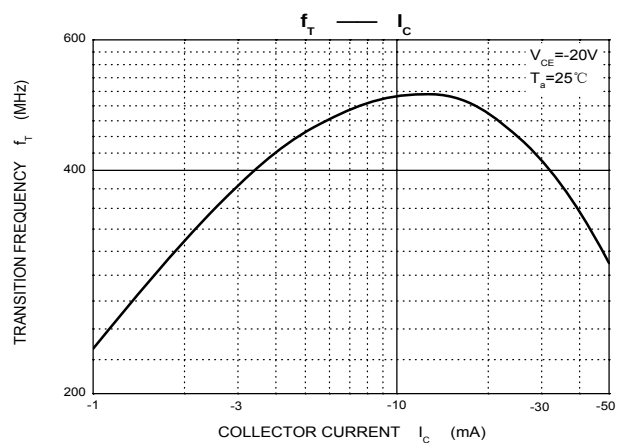
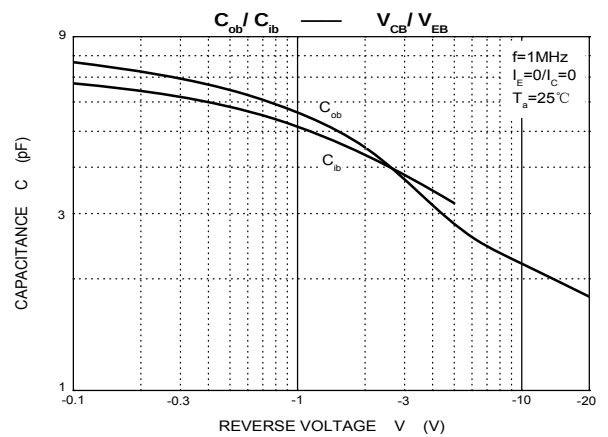
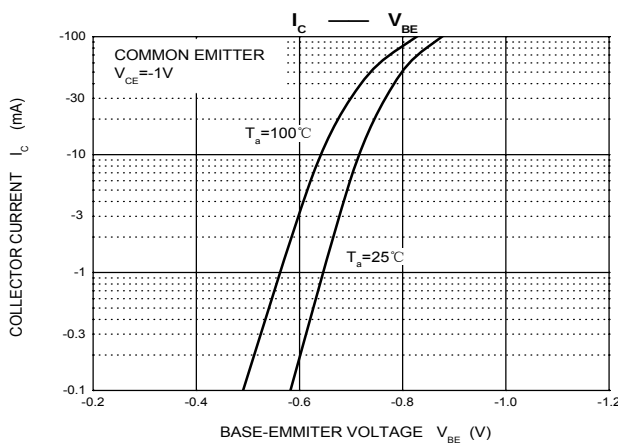
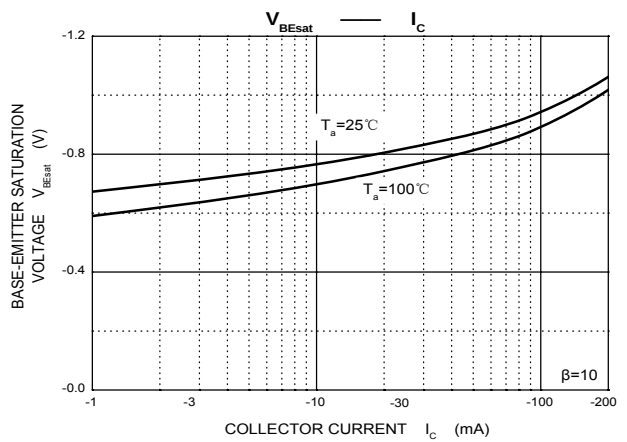
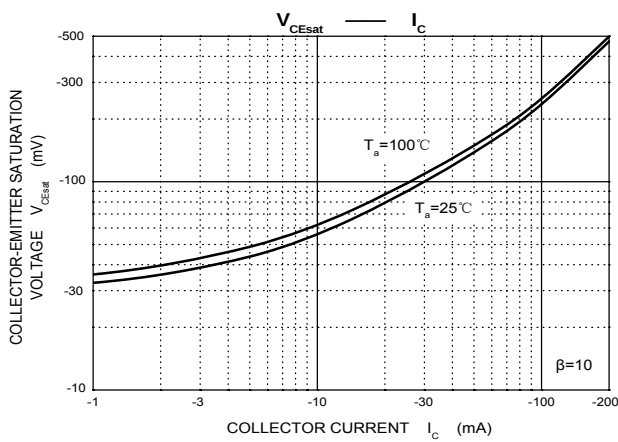
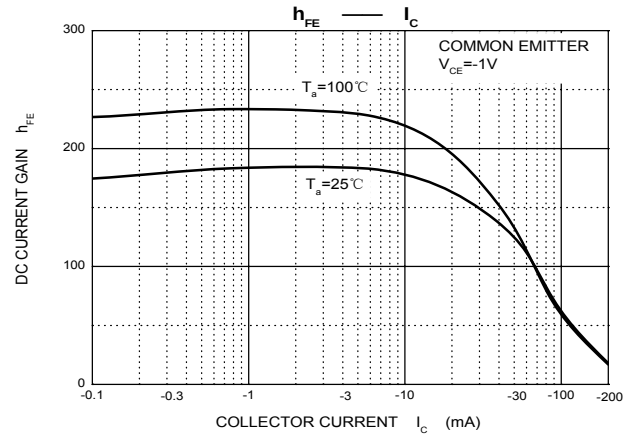
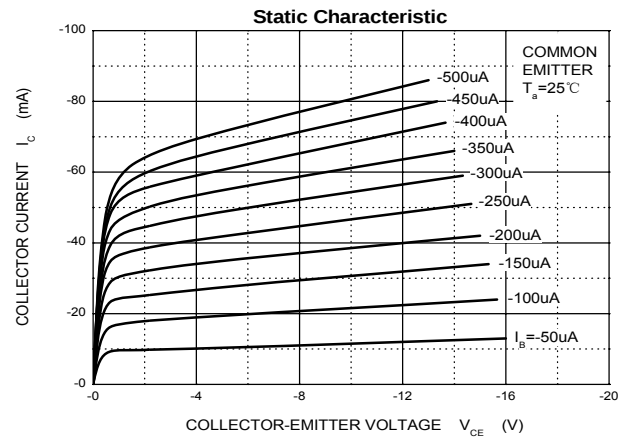
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}^*$	-60			V	$I_C = -5\mu\text{A}$, $I_E = 0$
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	-50			V	$I_C = -1\text{mA}$, $I_B = 0$
Emitter-base breakdown voltage	$V_{(BR)EBO}^*$	-5			V	$I_E = -50\mu\text{A}$, $I_C = 0$
Collector cut-off current	I_{CEX}^*			-50	nA	$V_{CE} = -30\text{V}$, $V_{BE(OFF)} = -3\text{V}$
Base cut-off current	I_{BL}^*			-50	nA	$V_{CE} = -30\text{V}$, $V_{BE(OFF)} = -3\text{V}$
DC current gain	h_{FE}^*	60				$V_{CE} = -1\text{V}$, $I_C = -0.1\text{mA}$
		80				$V_{CE} = -1\text{V}$, $I_C = -1\text{mA}$
		100		300		$V_{CE} = -1\text{V}$, $I_C = -10\text{mA}$
Collector-emitter saturation voltage	$V_{CE(sat)}^*$			-0.2	V	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$
				-0.3	V	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$
Base-emitter saturation voltage	$V_{BE(sat)}^*$	-0.65		-0.85	V	$I_C = -10\text{mA}$, $I_B = -1\text{mA}$
				-0.95	V	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$
Transition frequency	f_T	250			MHz	$V_{CE} = -20\text{V}$, $I_C = -10\text{mA}$, $f = 100\text{MHz}$
Collector output capacitance	C_{ob}			4.5	pF	$V_{CE} = -5\text{V}$, $I_E = 0$, $f = 1\text{MHz}$
Input capacitance	C_{ib}			10	pF	$V_{EB} = -0.5\text{V}$, $I_C = 0$, $f = 1\text{MHz}$
Delay time	t_d			35	ns	$V_{CC} = -3\text{V}$, $I_C = -10\text{mA}$,
Rise time	t_r			35	ns	$V_{EB(OFF)} = -0.5\text{V}$, $I_{B1} = -1\text{mA}$
Storage time	t_s			225	ns	$V_{CC} = -3\text{V}$, $I_C = -10\text{mA}$
Fall time	t_f			75	ns	$I_{B1} = I_{B2} = -1\text{mA}$

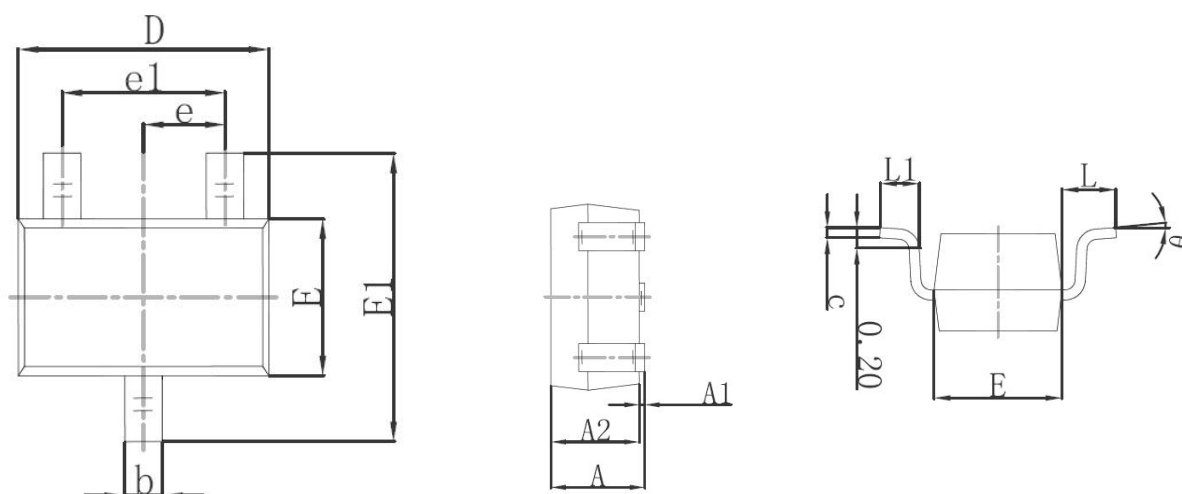
*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$

Marking: K5N

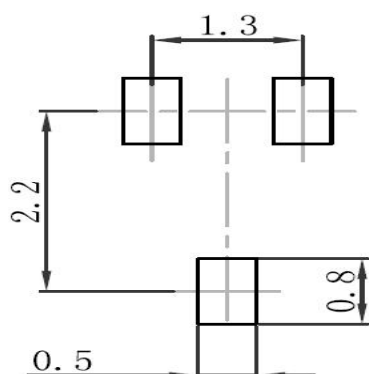
BIPOLAR TRANSISTOR (PNP)

Typical Characteristics

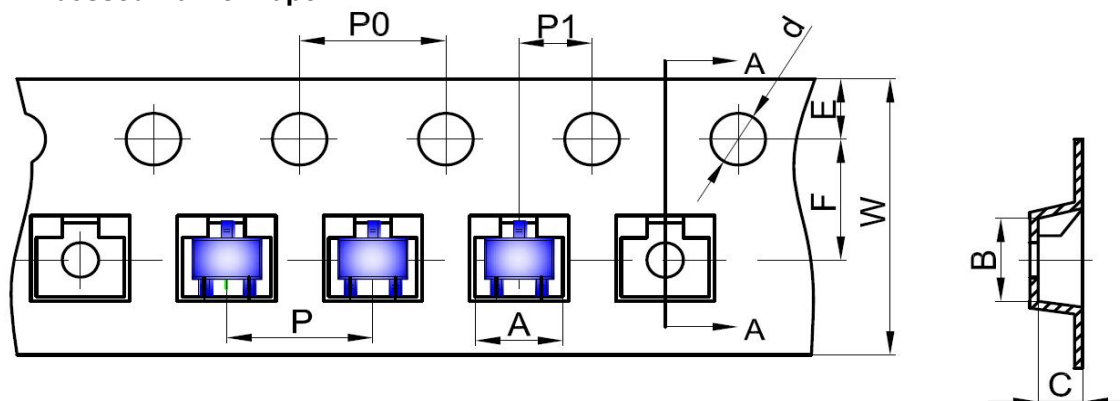


BIPOLAR TRANSISTOR (PNP)
SOT-323 Package Outline Dimensions


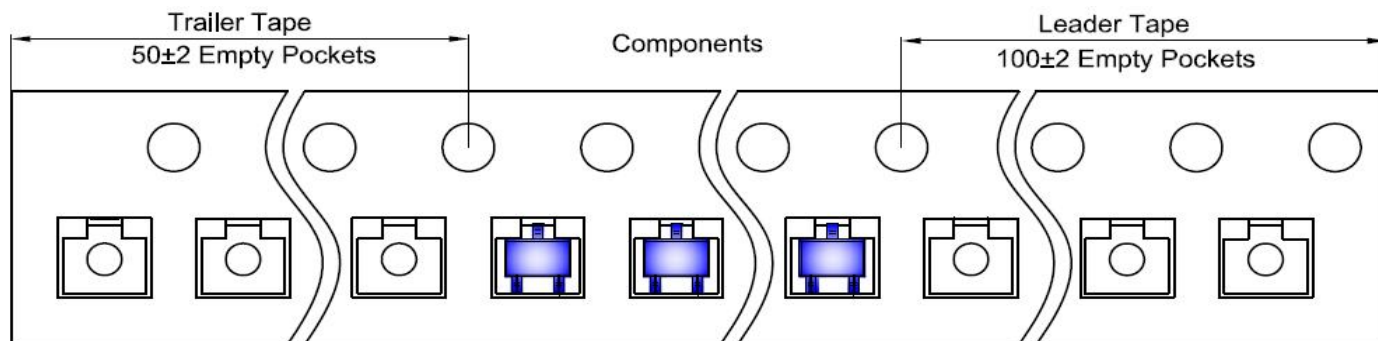
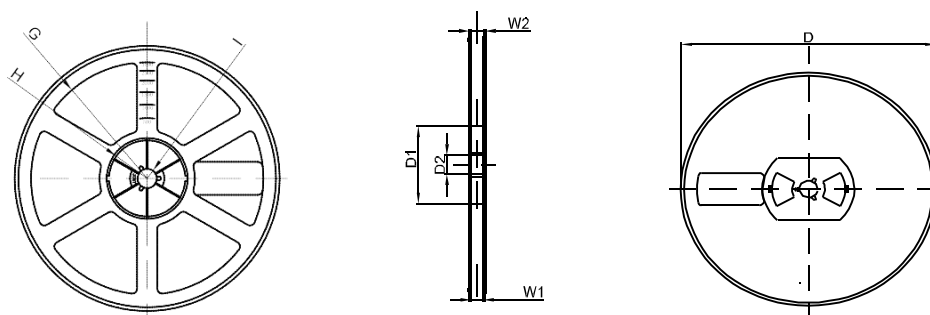
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-323 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

BIPOLAR TRANSISTOR (PNP)
SOT-323 Tape and Reel
SOT-323 Embossed Carrier Tape


	DIMENSIONS ARE IN MILLIMETER									
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-323	2.25	2.55	1.19	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-323 Tape Leader and Trailer

SOT-323 Reel


	DIMENSIONS ARE IN MILLIMETER							
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1